Notice of Allowability	Application No.	Applicant(s)	
	10/612,914	YEOM ET AL.	
	Examin r	Art Unit	
	Tu-Tu Ho	2818	
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate commo GHTS. This application is s	th the correspondence address this application. If not included	71110
1. A This communication is responsive to Papers filed 07/07/200	<u>03</u> .		*
2. The allowed claim(s) is/are <u>1-10</u> .			
3. The drawings filed on <u>07 July 2003</u> are accepted by the Ex	aminer.		
 4. Acknowledgment is made of a claim for foreign priority un a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 	been received.		
2. Certified copies of the priority documents have3. Copies of the certified copies of the priority doc			
International Bureau (PCT Rule 17.2(a)).	differits flave been received	in this national stage application	n from the
* Certified copies not received:			•
Applicant has THREE MONTHS FROM THE "MAILING DATE" on noted below. Failure to timely comply will result in ABANDONMITHIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to file ENT of this application.	a reply complying with the requ	irements
 A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which gives 	ted. Note the attached EXAs reason(s) why the oath or	MINER'S AMENDMENT or NO declaration is deficient.	TICE OF
6. \square CORRECTED DRAWINGS (as "replacement sheets") must	be submitted.		
(a) ☐ including changes required by the Notice of Draftsperso	on's Patent Drawing Review	(PTO-948) attached	
1) ☐ hereto or 2) ☐ to Paper No./Mail Date			•
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	Amendment / Comment or	in the Office action of	
Identifying indicia such as the application number (see 37 CFR 1.8 each sheet. Replacement sheet(s) should be labeled as such in th	34(c)) should be written on the header according to 37 CF	e drawings in the front (not the ba	ack) of
 DEPOSIT OF and/or INFORMATION about the depos attached Examiner's comment regarding REQUIREMENT F 	it of BIOLOGICAL MATE	RIAL must be submitted No	e the
		·	
Attachm nt(s)			•
1. Notice of References Cited (PTO-892)	5. Notice of Info	ormal Patent Application (PTO-1	(52)
2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	6. 🗌 Interview Su	mmary (PTO-413),	
 Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No./Mail Date <u>07/07/2003</u> 	Paper No.//), 7. 🔲 Examiner's A	Mail Date Amendment/Comment	
Examiner's Comment Regarding Requirement for Deposit	8. X Examiner's S	Statement of Reasons for Allowa	ance
of Biological Material	8. []] Other	,	-
		·	,
Supervisory Patent Examiner			
Te	echnology Center 2800		

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DETAILED ACTION

Priority

1. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Allowable Subject Matter

2. Claims 1-10 are allowable over the prior art of record.

The following is an examiner's statement of reasons for allowance: The prior art of record fails to teach or render obvious a ferroelectric memory device and a method of fabricating thereof having all exclusive limitations as recited in claims 1 and 6, comprising a substrate including a transistor, an interlevel dielectric layer (IDL) on the substrate, a connection plug in the IDL to contact an active region of the transistor, a lower electrode being connected to the connection plug, an insulation layer formed on the IDL, the insulation layer having a surface exposing a surface of the lower electrode and encompassing the lower electrode, a ferroelectric layer covering the insulation layer and the lower electrode, and an upper electrode on the ferroelectric layer, characterized in that the lower electrode includes a solid solution layer formed as an upper most layer of the lower electrode, and that the solid solution layer is doped with a metal.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue

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fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for

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Allowance."

Conclusion

3. The prior art made of record and not relied upon is considered pertinent to applicant's

disclosure. Copies of the references are not being furnished with this Office Action per MPEP

§ 707.05(a).

U.S. Patent 6,479,849 to Katori discloses a capacitor usable in a ferroelectric memory

device wherein the lower electrode of the capacitor comprises an adhesive layer including IrHf, a

precious metal layer including Ir, an oxygen inclusion layer including IrHfO, and a precious

metal layer including Ir.

4. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Tu-Tu Ho whose telephone number is (571) 272-1778. The

examiner can normally be reached on 6:30 am - 5:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, DAVID NELMS can be reached on (571) 272-1787. The fax phone numbers for the

organization where this application or proceeding is assigned are (703) 872-9306 for regular

communications and (703) 872-9306 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is (703) 308-1782.

Tu-Tu Ho May 20, 2004

Supervisory Patent Examiner Technology Center 2800